

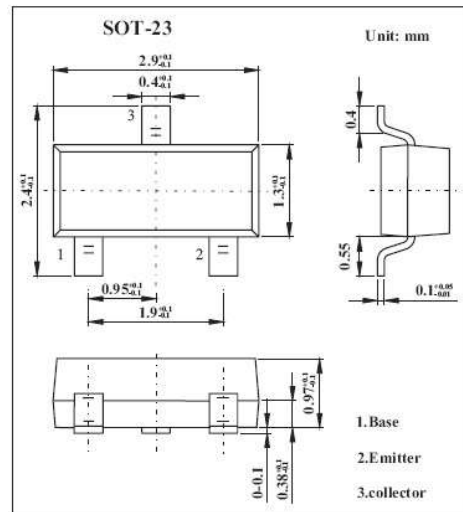
NPN General Purpose Transistors

BC849, BC850

Features

Low current (max. 100 mA)

Low voltage (max. 45 V).



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
collector-base voltage	V_{CB0}	30	V
		50	V
collector-emitter voltage	V_{CE0}	30	V
		45	V
emitter-base voltage	V_{EB0}	5	V
collector current (DC)	I_C	100	mA
peak collector current	I_{CM}	200	mA
peak base current	I_{BM}	200	mA
total power dissipation $T_{amb} \leq 25^\circ\text{C}^*$	P_{tot}	250	mW
storage temperature	T_{stg}	-65 to 150	$^\circ\text{C}$
junction temperature	T_j	150	$^\circ\text{C}$
operating ambient temperature	T_{amb}	-65 to 150	$^\circ\text{C}$
thermal resistance from junction to ambient *	$R_{\theta(j-a)}$	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
collector cut-off current	I _{CBO}	I _E = 0; V _{CB} = 30 V			15	nA
		I _E = 0; V _{CB} = 30 V; T _J = 150 °C			5	μA
emitter cut-off current	I _{EBO}	I _C = 0; V _{EB} = 5 V			100	nA
DC current gain BC849B; BC850B BC849C; BC850C	h _{FE}	I _C = 10 μA; V _{CE} = 5 V;		240		
		I _C = 2 mA; V _{CE} = 5 V;	200	290	450	
DC current gain BC849B; BC850B BC849C; BC850C	h _{FE}	I _C = 10 μA; V _{CE} = 5 V;	420	520	800	
		I _C = 2 mA; V _{CE} = 5 V;				
collector-emitter saturation voltage	V _{CEsat}	I _C = 10 mA; I _B = 0.5 mA		90	250	mV
		I _C = 100 mA; I _B = 5 mA		200	600	mV
base-emitter saturation voltage	V _{BEsat}	I _C = 10 mA; I _B = 0.5 mA; *1		700		mV
		I _C = 100 mA; I _B = 5 mA; *1		900		mV
base-emitter voltage	V _{BE}	I _C = 2 mA; V _{CE} = 5 V; *2	580	660	700	mV
		I _C = 10 mA; V _{CE} = 5 V; *2			770	mV
collector capacitance	C _c	I _E = I _E = 0; V _{CB} = 10 V; f = 1 MHz		2.5		pF
emitter capacitance	C _e	I _C = I _C = 0; V _{EB} = 500 mV; f = 1 MHz		11		pF
transition frequency	f _T	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz	100			MHz
noise figure	F	I _C = 200 μA; V _{CE} = 5 V; R _s = 2 kΩ, f = 10 Hz to 15.7 kHz			4	dB
		I _C = 200 μA; V _{CE} = 5 V; R _s = 2 kΩ, f = 1 kHz; B = 200 Hz			4	dB

*1 V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

*2 V_{BE} decreases by about 2 mV/K with increasing temperature.

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)